

CMPT930
SURFACE MOUNT
NPN SILICON TRANSISTOR



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT930 type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose and switching applications.

MARKING CODE: C1X

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CBO}	45
V_{CEO}	45
V_{EBO}	5.0
I_C	30
P_D	350
T_J, T_{stg}	-65 to +150
θ_{JA}	357

UNITS

V
V
V
mA
mW
$^\circ\text{C}$
$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=45\text{V}$		10	nA
I_{CEO}	$V_{CE}=5.0\text{V}$		10	nA
I_{CES}	$V_{CE}=45\text{V}$		10	nA
I_{EBO}	$V_{EB}=5.0\text{V}$		10	nA
BV_{CBO}	$I_C=10\mu\text{A}$	45		V
BV_{CEO}	$I_C=10\text{mA}$	45		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$		1.0	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$	0.6	1.0	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\mu\text{A}$	100	300	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=500\mu\text{A}$	150		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$		600	
f_T	$V_{CE}=5.0\text{V}, I_C=500\text{mA}, f=30\text{MHz}$	30		MHz
C_{ob}	$V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$		8.0	pF
NF	$V_{CE}=5.0\text{V}, I_C=10\text{mA}, R_S=10\text{k}\Omega,$ $f=10\text{Hz to } 15.7\text{kHz}$		3.0	dB

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SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

MARKING CODE: C1X

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R5 (27-January 2010)